

ABSTRACT

The present invention relates to a vapor phase growth method of a metal oxide dielectric film and capable of forming a metal oxide with excellent in both orientation and crystallinity on a plug at a low temperature and carries out film formation by introducing the organometal gases and an oxidizing gas into a vacuum chamber through separate introduction inlets while heating the substrate set in the vacuum chamber at 1×10^{-2} Torr or lower of the total pressure of the vacuum chamber. Further, the present invention is for carrying out film formation of a metal oxide dielectric film with a perovskite type crystal structure by changing film formation conditions and properly selecting optimum conditions for first film formation conditions for initial nuclei or layer formation and second film formation conditions for film formation of the perovskite type crystal structure further on the formed initial nuclei. The present invention further relates to a vapor phase growth apparatus to be employed for the vapor phase growth methods.